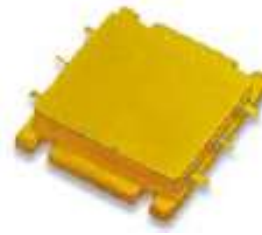


Performance

- Frequency: 0.3~2.0GHz
- Typical output power: 43dBm (CW)
- Typical Gain: 35dB
- Typical PAE: 30%
- Bias: 28V/-2.2V@0.4A
- Technology: 0.25um GaN HEMT

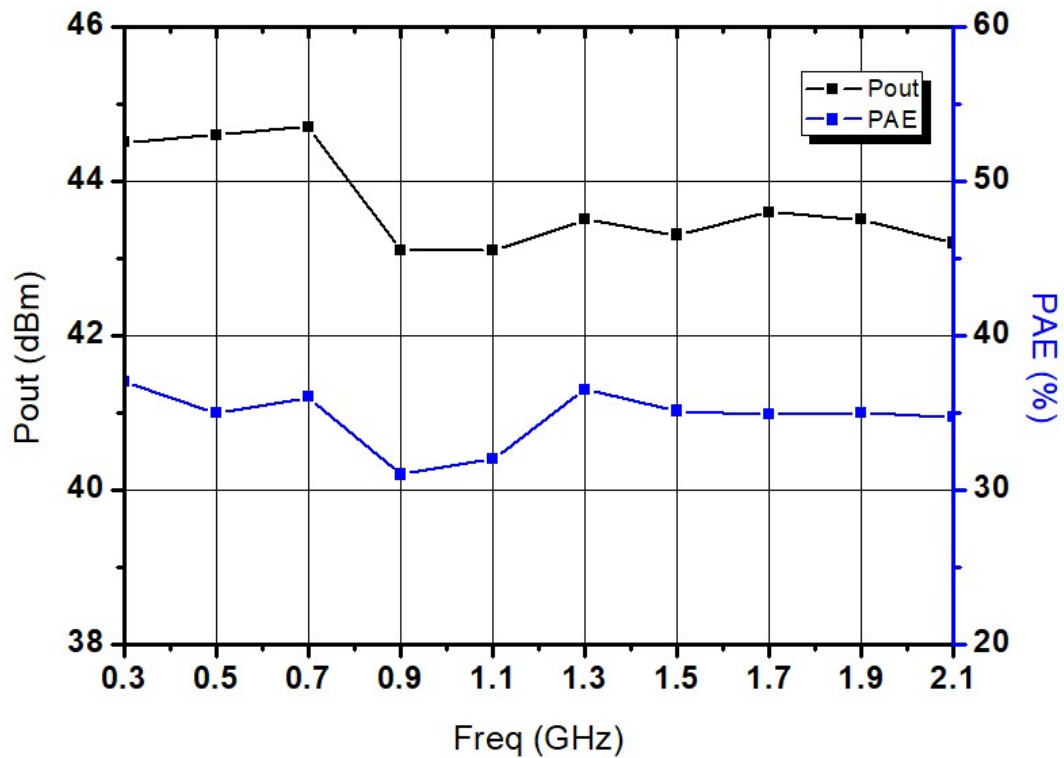


Electrical Specifications ($V_d=28V$, $I_d \approx 0.5A$, F: 0.3~2.0GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	43	-	-	dBm
Gp	Power Gain	35	-	-	dB
η	PAE	30	-	-	%
ΔG_p	Gain Flatness	-1.0	-	+1.0	dB

Test Curves (Large signal)

Output Power vs. Efficiency vs. Freq

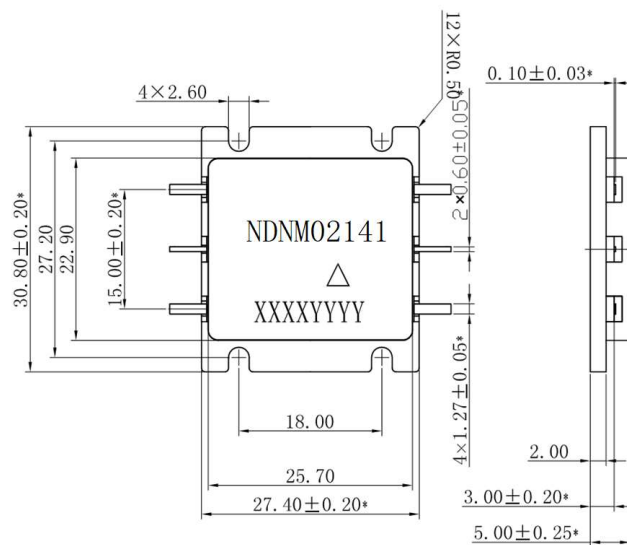


Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
Vds	Drain Voltage	40V	
Vgs	Gate Voltage	-5V	
Pd	DC Power	80W	25℃
Tch	Channel Temperature	225℃	
Tm	Mounting Temperature	300℃	1min, N2 protection
Tstg	Storage Temperature	-55~175℃	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Unit:mm

Application Circuits

